

**AMENDMENTS TO THE CLAIMS:**

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1. (Currently Amended) A method of forming a semiconductor substrate, comprising:  
forming a metal back-gate ~~over a substrate~~;  
forming a passivation layer on the metal back-gate to prevent the metal back-gate  
from reacting with radical species; and  
providing an intermediate gluing layer on said passivation layer to enhance adhesion  
between said metal back-gate and ~~said a~~ substrate,  
wherein a low temperature oxide (LTO) is deposited on said metal back-gate.
2. (Previously amended) The method of claim 1, wherein said intermediate gluing layer  
comprises one of a-Si, Si<sub>3</sub>N<sub>4</sub> and a combined layer of a-Si and Si<sub>3</sub>N<sub>4</sub>.
3. (Original) The method of claim 1, wherein said forming of said metal back-gate  
includes depositing W, and  
said forming of said passivation layer is performed after said W deposition, said  
passivation layer being a thin W passivation layer.
4. (Previously amended) The method of claim 3, wherein said depositing of said W  
comprises a physical vapor deposition (PVD) of W.
5. (Original) The method of claim 3, wherein said depositing of said W comprises a  
chemical vapor deposition (CVD) of W.
6. (Currently Amended) A method of forming a semiconductor substrate, comprising:  
forming a metal back-gate ~~over a substrate~~;  
forming a passivation layer on the metal back-gate to prevent the metal back-gate  
from reacting with radical species; and  
providing an intermediate gluing layer on said passivation layer to enhance adhesion  
between said metal back-gate and ~~said a~~ substrate,  
wherein said forming of said metal back-gate comprises:

c<sup>1</sup> 8                   conducting UHV desorption of native oxide on W under a pressure of  $10^{-9}$  torr  
9                   at 750°C for 5 minutes;

10                   forming a monolayer of W-Si silicide at 625°C for 1.5 minutes using  $\text{SiH}_4$   
11                   such that a bare W surface reacts with Si to form a monolayer of W-Si; and

12                   performing nitridation of W-Si at 750°C for 30 minutes with  $\text{NH}_3$  and reacting  
13                   active  $\text{NH}_2$  with W-Si to form W-Si-N.

7.       (Original) The method of claim 1, wherein said metal back-gate is formed of a metal having a high melting temperature to withstand thermal treatment during semiconductor processing.

8.       (Original) The method of claim 7, wherein said metal back-gate comprises one of tungsten and titanium nitride.

9.       (Original) The method of claim 1, wherein said substrate comprises a silicon-on-insulator substrate having a gate oxide formed thereon.

10.      (Original) The method of claim 9, wherein said metal back-gate comprises a tungsten layer, said tungsten layer being deposited on the gate oxide.

11.      (Currently Amended) The method of claim 1, wherein the metal back-gate comprises a W layer, and wherein a said low temperature oxide (LTO) is deposited on the W layer.

12.      (Previously amended) The method of claim 1, wherein a multilayer stack is formed on said substrate, wherein said substrate with said multilayer stack is bonded to a silicon substrate and annealed to strengthen the bond across the bonding interface.

13.      (Original) The method of claim 11, wherein said W layer is passivated before the LTO deposition to prevent the reaction of tungsten with oxygen and the delamination at the W- $\text{SiO}_2$  interface.

c1 14. (Original) The method of claim 1, further comprising annealing said metal back-gate and said substrate.

15. (Original) The method of claim 14, wherein said annealing occurs at temperatures below 1100 °C.

16. (Previously amended) The method of claim 15, wherein annealing conditions including any of a ramp-up rate, a ramp-down rate, a stabilization temperature, and a stabilization temperature time are optimized to minimize stress induced by thermal mismatch of different materials of said metal back-gate, said substrate, said passivation layer and said intermediate gluing layer.

17. (Previously amended) The method of claim 1, wherein said intermediate gluing layer comprises a Si-based intermediate layer.

1 18. (Currently Amended) A method of forming a semiconductor substrate, comprising:  
2 forming a metal back-gate ~~over a substrate~~; and  
3 providing a passivation layer between ~~said a~~ substrate and said metal back-gate to  
4 enhance adhesion therebetween,  
5 wherein a low temperature oxide (LTO) is deposited on said metal back-gate.

1 19. (Currently Amended) A method of forming a semiconductor substrate, comprising:  
2 growing a gate oxide on a silicon-on-insulator (SOI) material;  
3 depositing a refractory metal onto said gate oxide; and  
4 forming a passivation layer on said refractory metal,  
5 wherein a low temperature oxide (LTO) is deposited on the refractory metal.

20. (Original) The method of claim 19, further comprising:  
depositing an insulator on said metal to form a multi-layer stack;  
bonding said multi-layer stack to a second substrate, to form a bonded structure; and  
annealing said bonded structure.

d 21. (Original) The method according to claim 19, wherein said insulator comprises one of a low temperature oxide, SiN and AlOx.

22-35. (Previously canceled)

36. (Canceled)

37. (Canceled)

38. (Canceled)

39. (Currently Amended) A The method of claim 1 forming a semiconductor substrate, comprising:

forming a metal back-gate;

forming a passivation layer on the metal back-gate to prevent the metal back-gate from reacting with radical species; and

providing an intermediate gluing layer on said passivation layer to enhance adhesion between said metal back-gate and a substrate,

wherein said providing said intermediate gluing layer on said passivation layer comprises growing said intermediate layer by in-situ ultra high vacuum chemical vapor deposition (UHV CVD) growth of metal -Si-N.

40. (Previously added) The method of claim 39, wherein said metal comprises tungsten.

41. (Currently Amended) A The method of claim 18 forming a semiconductor substrate, comprising:

forming a metal back-gate; and

providing a passivation layer between a substrate and said metal back-gate to enhance adhesion therebetween,

wherein said providing said passivation layer comprises growing said passivation layer by in-situ ultra high vacuum chemical vapor deposition (UHV CVD) growth of metal-

Si-N.

42. (Previously added) The method of claim 41, wherein said metal comprises tungsten.

43. (Currently Amended) A The method of claim 19 forming a semiconductor substrate, comprising:

growing a gate oxide on a silicon-on-insulator (SOI) material;

depositing a refractory metal onto said gate oxide; and

forming a passivation layer on said refractory metal,

wherein said forming said passivation layer comprises growing said passivation layer by in-situ ultra high vacuum chemical vapor deposition (UHV CVD) growth of metal-Si-N.

44. (Previously added) The method of claim 43, wherein said metal comprises tungsten.

45. (New) A method of forming a semiconductor substrate, comprising:

forming a metal back-gate; and

providing a passivation layer between a substrate and said metal back-gate to enhance adhesion therebetween,

wherein said passivation layer is grown in-situ such that subsequent oxidation of a metal is substantially prevented.

46. (New) The method of claim 45, wherein said in-situ growth of said passivation layer comprises a chemical vapor deposition (CVD) growth of metal -Si-N.

47. (New) The method of claim 46, wherein said chemical vapor deposition comprises an ultra high vacuum (UHV) deposition.

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